PROCESS CP219

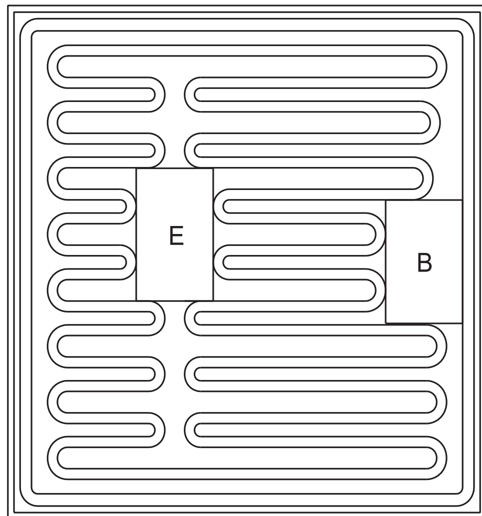
Power Transistor

NPN - High Current Transistor Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	83 x 83 MILS
Die Thickness	11 MILS
Base Bonding Pad Area	13.2 x 19.7 MILS
Emitter Bonding Pad Area	13.2 x 21.2 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE COLLECTOR R0

GROSS DIE PER 4 INCH WAFER

1,670

PRINCIPAL DEVICE TYPES

2N5336
2N5337
2N5338
2N5339
2N5427
2N5428
2N5429
2N5430
D44H11
CJD44H11

PROCESS CP219

Typical Electrical Characteristics